### 查询SN74LVC1G3157YZPR供应商

### 捷多邦,专业PCB打样工厂,24小时加**SN环体**\_VC1G3157 SINGLE-POLE, DOUBLE-THROW ANALOG SWITCH

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- **DBV OR DCK PACKAGE** 1.65-V to 5.5-V V<sub>CC</sub> Operation (TOP VIEW) Useful for Both Analog and Digital Applications B2 S Specified Break-Before-Make Switching 5 VCC GND 2 **Rail-to-Rail Signal Handling** B1 [ 3 4 Π Α **High Degree of Linearity** High Speed, Typically 0.5 ns YEP OR YZP PACKAGE  $(V_{CC} = 3 V, C_{L} = 50 pF)$ (BOTTOM VIEW) Low On-State Resistance, Typically  $\approx 6 \Omega$ R1  $^{\circ}3$ 4 C  $(V_{CC} = 4.5 V)$ GND 02 50 Vcc Latch-Up Performance Exceeds 100 mA Per **B**2 01 6 C JESD 78, Class II ESD Protection Exceeds JESD 22 2000-V Human-Body Model (A114-A)
- 200-V Machine Model (A115-A)
- 1000-V Charged-Device Model (C101)

### description/ordering information

This single-pole, double-throw (SPDT) analog switch is designed for 1.65-V to 5.5-V V<sub>CC</sub> operation.

The SN74LVC1G3157 can handle both analog and digital signals. The device permits signals with amplitudes of up to  $V_{CC}$  (peak) to be transmitted in either direction.

Applications include signal gating, chopping, modulation or demodulation (modem), and signal multiplexing for analog-to-digital and digital-to-analog conversion systems.

#### **ORDERING INFORMATION**

	т <sub>А</sub>	PACKAGET		ORDERABLE PART NUMBER	TOP-SIDE MARKING <sup>‡</sup>	
		NanoStar™ – WCSP (DSBGA) 0.23-mm Large Bump – YEP	Tape and reel	SN74LVC1G3157YEPR	C5	
-40	–40°C to 85°C	Na <mark>noFree™ –</mark> WCSP (DSBGA) 0.23-mm Large Bump – YZP (Pb-free)	Tape and Teer	SN74LVC1G3157YZPR	05_	
-		SOT (SOT-23) – DBV	Tape and reel	SN74LVC1G3157DBVR	CC5_	
		SOT (SC-70) – DCK	Tape and reel	SN74LVC1G3157DCKR	C5_	

<sup>†</sup> Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

DBV/DCK: The actual top-side marking has one additional character that designates the assembly/test site. YEP/YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site. Pin 1 identifier indicates solder-bump composition (1 = SnPb, • = Pb-free).



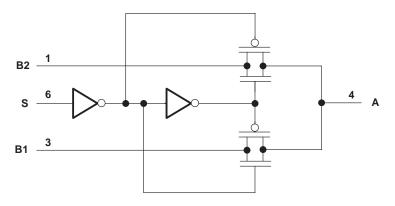
Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



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FUNCTION TABLE						
CONTROL INPUT S	ON CHANNEL					
L	B1					
н	B2					

logic diagram (positive logic)



### absolute maximum ratings over operating free-air temperature range (unless otherwise noted)<sup>†</sup>

Supply voltage range, V <sub>CC</sub> (see Note 1)0.	.5 V to 6.5 V
Control input voltage range, V <sub>IN</sub> (see Notes 1 and 2)0.	
Switch I/O voltage range, V <sub>I/O</sub> (see Notes 1, 2, 3, and 4)0.5 V to	V <sub>CC</sub> + 0.5 V
Control input clamp current, I <sub>IK</sub> (V <sub>IN</sub> < 0)	–50 mA
I/O port diode current, $I_{IOK}$ ( $V_{I/O} < 0$ or $V_{I/O} > V_{CC}$ )	±50 mA
On-state switch current, $I_{I/O}$ ( $V_{I/O} = 0$ to $V_{CC}$ ) (see Note 5)	±128 mA
Continuous current through V <sub>CC</sub> or GND	±100 mA
Package thermal impedance, $\theta_{JA}$ (see Note 6): DBV package	165°C/W
DCK package	259°C/W
YEP/YZP package	123°C/W
Storage temperature range, T <sub>stg</sub> 65	°C to 150°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltages are with respect to ground unless otherwise specified.
  - 2. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
  - 3. This value is limited to 5.5 V maximum.
  - 4.  $V_I$ ,  $V_O$ ,  $V_A$ , and  $V_{Bn}$  are used to denote specific conditions for  $V_{I/O}$ .
  - 5. II, IO, IA, and IBn are used to denote specific conditions for II/O.
  - 6. The package thermal impedance is calculated in accordance with JESD 51-7.



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### recommended operating conditions (see Note 7)

			MIN	MAX	UNIT
VCC		1.65	5.5	V	
V <sub>I/O</sub>			0	VCC	V
VIN			0	5.5	V
	High-level input voltage, control input	V <sub>CC</sub> = 1.65 V to 1.95 V	$V_{CC} \times 0.75$		V
VIH	High-level input voltage, control input	$V_{CC} = 2.3 \text{ V to } 5.5 \text{ V}$	$V_{CC} \times 0.7$		v
	Low-level input voltage, control input	V <sub>CC</sub> = 1.65 V to 1.95 V		$V_{CC} \times 0.25$	V
VIL	Low-level input voltage, control input	$V_{CC} = 2.3 \text{ V to } 5.5 \text{ V}$		$V_{CC} \times 0.3$	v
		$V_{CC}$ = 1.65 V to 1.95 V		20	
Δt/Δv	Input transition rise/fall time	$V_{CC}$ = 2.3 V to 2.7 V		20	ns/V
ΔυΔν		V <sub>CC</sub> = 3 V to 3.6 V		10	115/ V
		$V_{CC}$ = 4.5 V to 5.5 V		10	
TA			-40	85	°C

NOTE 7: All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



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### electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

	PARAMETER		TES	Vcc	MIN TYP <sup>†</sup>	MAX	UNIT		
				V <sub>I</sub> = 0 V	I <sub>O</sub> = 4 mA		11	20	
				V <sub>I</sub> = 1.65 V	I <sub>O</sub> = -4 mA	1.65 V	15	50	
				V <sub>I</sub> = 0 V	IO = 8 mA	2.3 V	8	12	
r <sub>on</sub>				V <sub>I</sub> = 2.3 V	I <sub>O</sub> = –8 mA		11	30	
	On-state switch resistant	witch resistance‡	See Figures 1 and 2	V <sub>I</sub> = 0 V	I <sub>O</sub> = 24 mA	3 V	7	9	Ω
				V <sub>I</sub> = 3 V	l <sub>O</sub> = -24 mA	3 V	9	20	
				$V_{I} = 0 V$	I <sub>O</sub> = 30 mA		6	7	
				V <sub>I</sub> = 2.4 V	$I_{O} = -30 \text{ mA}$	4.5 V	7	12	
				V <sub>I</sub> = 4.5 V	$I_{O} = -30 \text{ mA}$		7	15	
					$I_A = -4 \text{ mA}$	1.65 V		140	
-	On-state switch resistance	ce	$0 \le V_{Bn} \le V_{CC}$		I <sub>A</sub> = -8 mA	2.3 V		45	0
rrange	over signal range‡§		(see Figures 1 a	nd 2)	I <sub>A</sub> = -24 mA	3 V		18	Ω
				-	I <sub>A</sub> = -30 mA	4.5 V		10	
∆r <sub>on</sub>				V <sub>Bn</sub> = 1.15 V	$I_A = -4 \text{ mA}$	1.65 V	0.5		
	Difference of on-state resistance between switches‡¶#		See Figure 1	V <sub>Bn</sub> = 1.6V	I <sub>A</sub> = –8 mA	2.3 V	0.1		Ω
				V <sub>Bn</sub> = 2.1 V	I <sub>A</sub> = -24 mA	3 V	0.1		
				V <sub>Bn</sub> = 3.15 V	I <sub>A</sub> = -30 mA	4.5 V	0.1		
	ON resistance flatness‡¶∥				I <sub>A</sub> = -4 mA	1.65 V	110		Ω
<b>F</b> ( <b>f</b> ) ()					I <sub>A</sub> = –8 mA	2.3 V	26		
ron(flat)			$I_{A} = -24$ r		$I_A = -24 \text{ mA}$	3 V	9		52
					I <sub>A</sub> = -30 mA	4.5 V	4		
1 "*	Off-state switch leakage	current	$0 \le V_{I}, V_{O} \le V_{CO}$	(see Figure 3)		1.65 V		±1	μA
<sup>I</sup> off <sup>☆</sup>	On state switch leakage	ourrent		,, (See Figure 0)		to 5.5 V	±0.05	±1†	μ
I <sub>S(on)</sub>	On-state switch leakage	current	$V_{I} = V_{CC}$ or GNE	),		5.5 V		±1	μA
<sup>1</sup> S(01)	on state switch leakage	ourront	V <sub>O</sub> = Open (see	Figure 4)		0.0 V		±0.1†	μπ
IIN	Control input current		0 ≤ VIN ≤ VCC			0 V to		±1	μA
·IIN			$0 \ge 0$ IN $\ge 0$ CC			5.5 V	±0.05	±1†	μΛ
ICC	Supply current		$V_{IN} = V_{CC}$ or GN			5.5 V	1	10	μA
∆ICC	Supply-current change		$V_{IN} = V_{CC} - 0.6 V$			5.5 V		500	μΑ
C <sub>in</sub>	Control input capacitance	S				5 V	2.7		pF
C <sub>io(off)</sub>	Switch input/output capacitance	Bn				5 V	5.2		pF
Circlary	Switch input/output	Bn				5.1/	17.3		۶E
C <sub>io(on)</sub>	capacitance A					5 V	17.3		pF

 $^{+}T_{A} = 25^{\circ}C$ 

\* Measured by the voltage drop between I/O pins at the indicated current through the switch. ON resistance is determined by the lower of the voltages on the two (A or B) ports.

§ Specified by design

 $\int \Delta r_{on} = r_{on}(max) - r_{on}(min)$  measured at identical V<sub>CC</sub>, temperature, and voltage levels. # This parameter is characterized, but not tested in production.

|| Flatness is defined as the difference between the maximum and minimum values of ON resistance over the specified range of conditions.

 $^{\star}$  I<sub>off</sub> is the same as I<sub>S(off)</sub> (off-state switch leakage current).



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UNIT

MHz

dB

dB

pC

%

3

7

#### analog switch characteristics, T<sub>A</sub> = 25°C FROM то **TEST CONDITIONS** TYP PARAMETER Vcc (OUTPUT) (INPUT) 1.65 V 300 $R_L = 50 \Omega$ , 2.3 V 300 Frequency response A or Bn Bn or A fin = sine wave (switch on)<sup>†</sup> 3 V 300 (see Figure 6) 4.5 V 300 1.65 V -54 $R_L = 50 \Omega$ , 2.3 V -54 Crosstalk f<sub>in</sub> = 10 MHz (sine wave) B1 or B2 B2 or B1 (between switches)‡ -54 3 V (see Figure 7) 4.5 V -54 -57 1.65 V $C_{I} = 5 \text{ pF}, R_{I} = 50 \Omega,$ -57 2.3 V Feed-through attenuation A or Bn Bn or A fin = 10 MHz (sine wave) (switch off)<sup>‡</sup> -57 3 V (see Figure 8) 4.5 V -57 3.3 V $C_{I} = 0.1 \text{ nF}, R_{I} = 1 \text{ M}\Omega,$ S А Charge injection§ (see Figure 9) 5 V 1.65 V 0.1 $V_I = 0.5 V p-p, R_L = 600 \Omega$ , 2.3 V 0.025 $f_{in} = 600 \text{ Hz to } 20 \text{ kHz}$ Total harmonic distortion A or Bn Bn or A (sine wave) 3 V 0.015 (see Figure 10) 4.5 V 0.01

<sup>†</sup> Adjust f<sub>in</sub> voltage to obtain 0 dBm at output. Increase f<sub>in</sub> frequency until dB meter reads –3 dB.

<sup>‡</sup>Adjust fin voltage to obtain 0 dBm at input.

§ Specified by design

#### switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 5 and 11)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> = ± 0.1		V <sub>CC</sub> = ± 0.2		= ۷ <sub>CC</sub> ± 0.		= V <sub>CC</sub> ± 0.	= 5 V 5 V	UNIT
		(001-01)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
tpd¶	A or Bn	Bn or A		2		1.2		0.8		0.3	ns
t <sub>en</sub> #	s	Bn	7	24	3.5	14	2.5	7.6	1.7	5.7	20
t <sub>dis</sub>	5	DII	3	13	2	7.5	1.5	5.3	0.8	3.8	ns
<sup>t</sup> B-M <sup>☆</sup>			0.5		0.5		0.5		0.5		ns

Itod is the slower of tPLH or tPHL. The propagation delay is calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance when driven by an ideal voltage source (zero output impedance).

#ten is the slower of tPZL or tPZH.

Il t<sub>dis</sub> is the slower of tpLZ or tpHZ.

\* Specified by design



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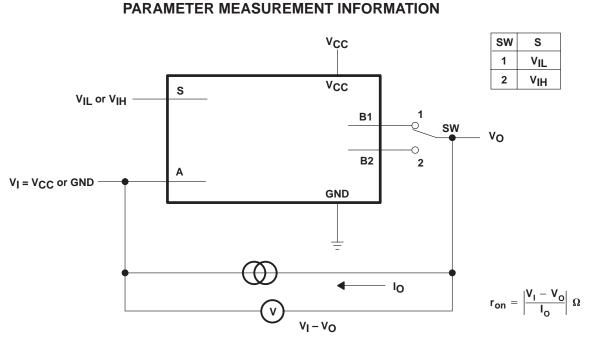


Figure 1. On-State Resistance Test Circuit

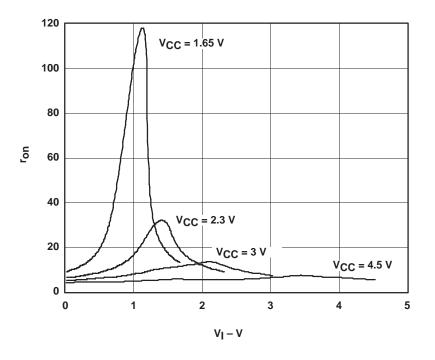
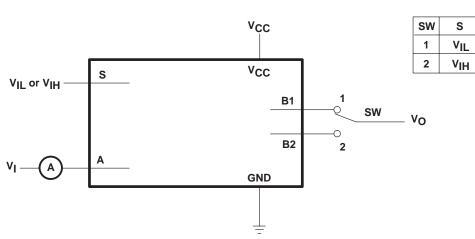


Figure 2. Typical  $r_{on}$  as a Function of Input Voltage (VI) for VI = 0 to V<sub>CC</sub>



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#### PARAMETER MEASUREMENT INFORMATION

 $\begin{array}{l} \text{Condition 1: } V_I = \text{GND}, \, V_O = V_{CC} \\ \text{Condition 2: } V_I = V_{CC}, \, V_O = \text{GND} \end{array}$ 

### Figure 3. Off-State Switch Leakage-Current Test Circuit

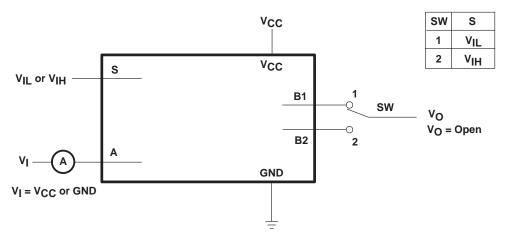
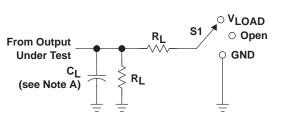


Figure 4. On-State Switch Leakage-Current Test Circuit

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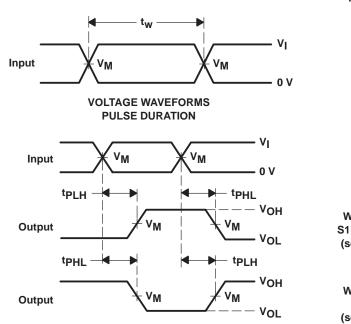
TEST	S1
<sup>t</sup> PLH <sup>/t</sup> PHL	Open
<sup>t</sup> PLZ <sup>/t</sup> PZL	V <sub>LOAD</sub>
<sup>t</sup> PHZ <sup>/t</sup> PZH	GND

٧ı

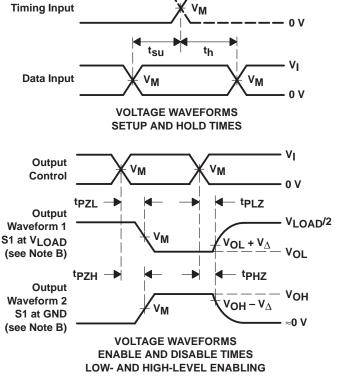
LOAD CIRCUIT

N.	INPUTS		V	V	0		V
Vcc	v	t <sub>r</sub> /t <sub>f</sub>	VМ	VLOAD	сL	RL	$v_\Delta$
$1.8~V\pm0.15~V$	V <sub>CC</sub>	≤2 ns	V <sub>CC</sub> /2	$2 \times V_{CC}$	50 pF	<b>500</b> Ω	0.3 V
2.5 V $\pm$ 0.2 V	VCC	≤2 ns	V <sub>CC</sub> /2	$2 \times V_{CC}$	50 pF	<b>500</b> Ω	0.3 V
3.3 V $\pm$ 0.3 V	Vcc	≤2.5 ns	V <sub>CC</sub> /2	$2 \times V_{CC}$	50 pF	<b>500</b> Ω	0.3 V
5 V $\pm$ 0.5 V	Vcc	≤2.5 ns	V <sub>CC</sub> /2	$2 \times V_{CC}$	50 pF	<b>500</b> Ω	0.3 V

PARAMETER MEASUREMENT INFORMATION



#### VOLTAGE WAVEFORMS PROPAGATION DELAY TIMES INVERTING AND NONINVERTING OUTPUTS



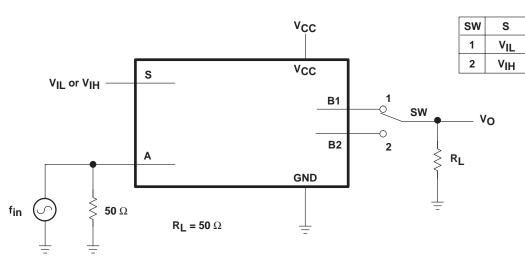
NOTES: A.  $C_L$  includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz, Z<sub>O</sub> = 50  $\Omega$ .
- D. The outputs are measured one at a time with one transition per measurement.
- E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
- F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
- G.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{pd}$ .
- H. All parameters and waveforms are not applicable to all devices.

### Figure 5. Load Circuit and Voltage Waveforms



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#### PARAMETER MEASUREMENT INFORMATION

### Figure 6. Frequency Response (Switch On)

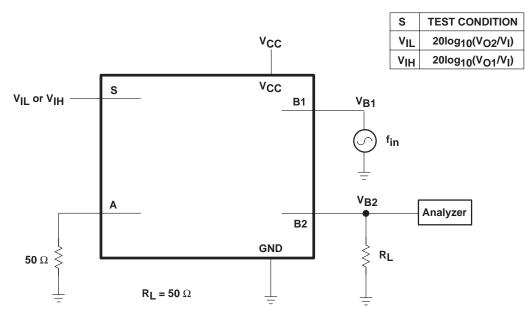
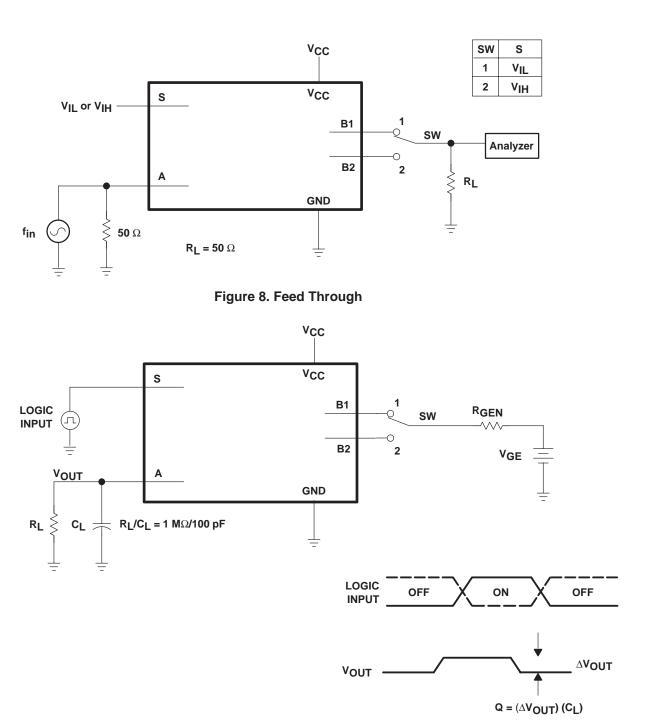


Figure 7. Crosstalk (Between Switches)



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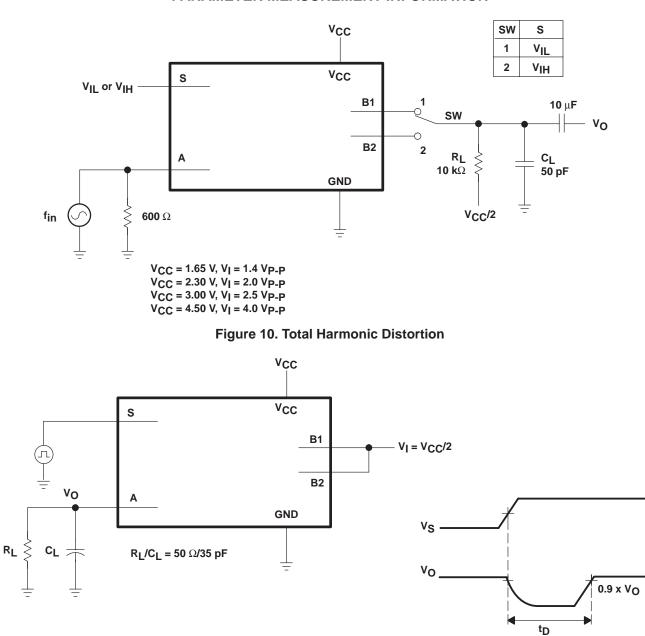


PARAMETER MEASUREMENT INFORMATION

Figure 9. Charge-Injection Test



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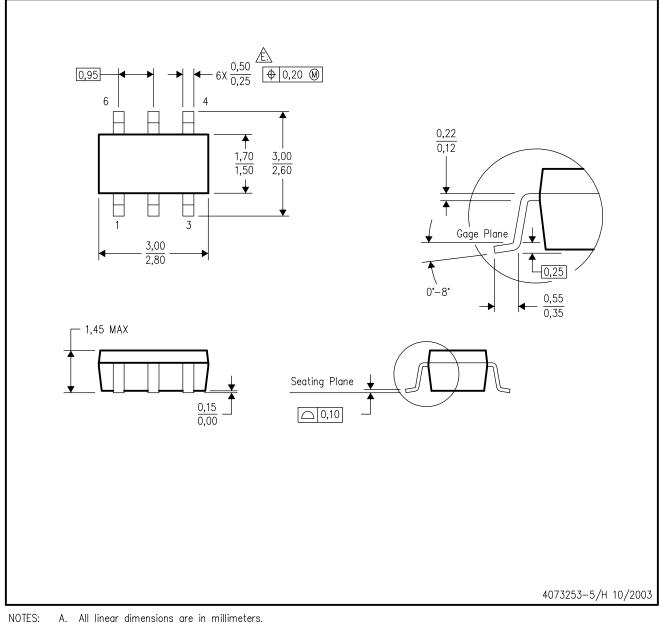
PARAMETER MEASUREMENT INFORMATION

Figure 11. Break-Before-Make Internal Timing



DBV (R-PDSO-G6)

# PLASTIC SMALL-OUTLINE PACKAGE



A. All linear dimensions are in millimeters.

- This drawing is subject to change without notice. Β.
- C. Body dimensions do not include mold flash or protrusion.D. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
- E Falls within JEDEC MO-178 Variation AB, except minimum lead width.

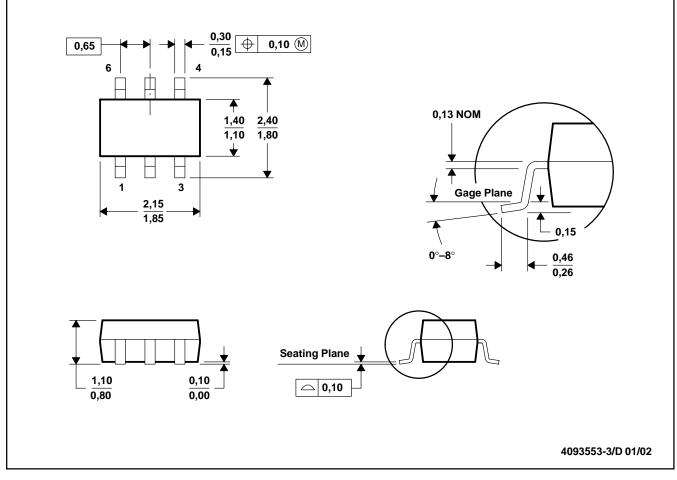


# **MECHANICAL DATA**

MPDS114 - FEBRUARY 2002

#### DCK (R-PDSO-G6)

#### PLASTIC SMALL-OUTLINE PACKAGE



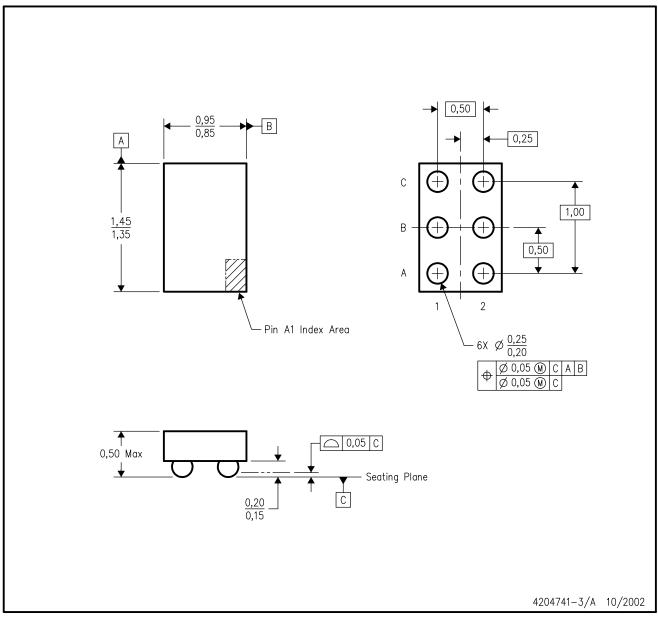
NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. Falls within JEDEC MO-203



YZP (R-XBGA-N6)

DIE-SIZE BALL GRID ARRAY



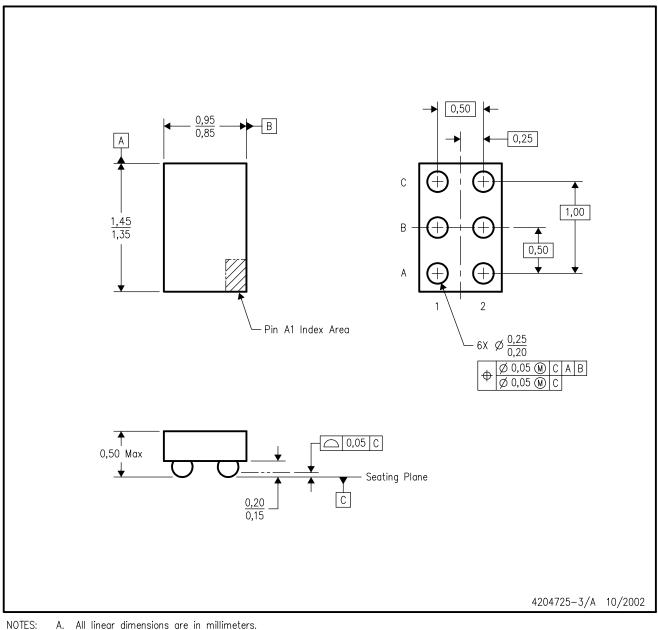
NOTES:

- A. All linear dimensions are in millimeters.B. This drawing is subject to change without notice.
- C. NanoFree™ package configuration.
- D. This package is lead-free. Refer to the 6 YEP package (drawing 4204725) for tin-lead (SnPb).

NanoFree is a trademark of Texas Instruments.

YEP (R-XBGA-N6)

# DIE-SIZE BALL GRID ARRAY



NOTES:

- This drawing is subject to change without notice. Β.
- C. NanoStar™ package configuration.
- D. This package is tin-lead (SnPb). Refer to the 6 YZP package (drawing 4204741) for lead-free.

NanoStar is a trademark of Texas Instruments.

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